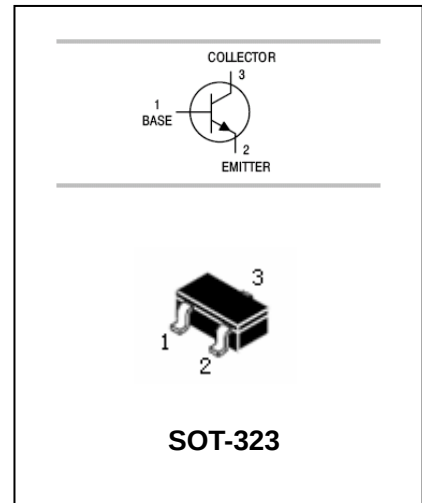


NPN Silicon Epitaxial Planar Transistor

2PD601AW

FEATURES

- Collector Current.($I_C = 100\text{mA}$)
- Excellent H_{FE} Linearity.
- Power dissipation.($P_C = 200\text{mW}$)



APPLICATIONS

- General purpose application.

ORDERING INFORMATION

Type No.	Marking	Package Code
2PD601AW	6D/6E/6F	SOT-323

MAXIMUM RATING @ $T_a = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	100	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^\circ\text{C}$

NPN Silicon Epitaxial Planar Transistor**2PD601AW****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.01	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.01	μA
DC current gain	h_{FE}	$V_{CE}=10V, I_C=2mA$ 2PD601AQW 2PD601ARW 2PD601ASW	160 210 290		260 340 460	
		$V_{CE}=2V, I_C=100mA$	90			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.5	V
Transition frequency	f_T	$V_{CE}=6V, I_C=2mA$ $f=100MHz$ 2PD601AQW 2PD601ARW 2PD601ASW	100 120 140			MHz

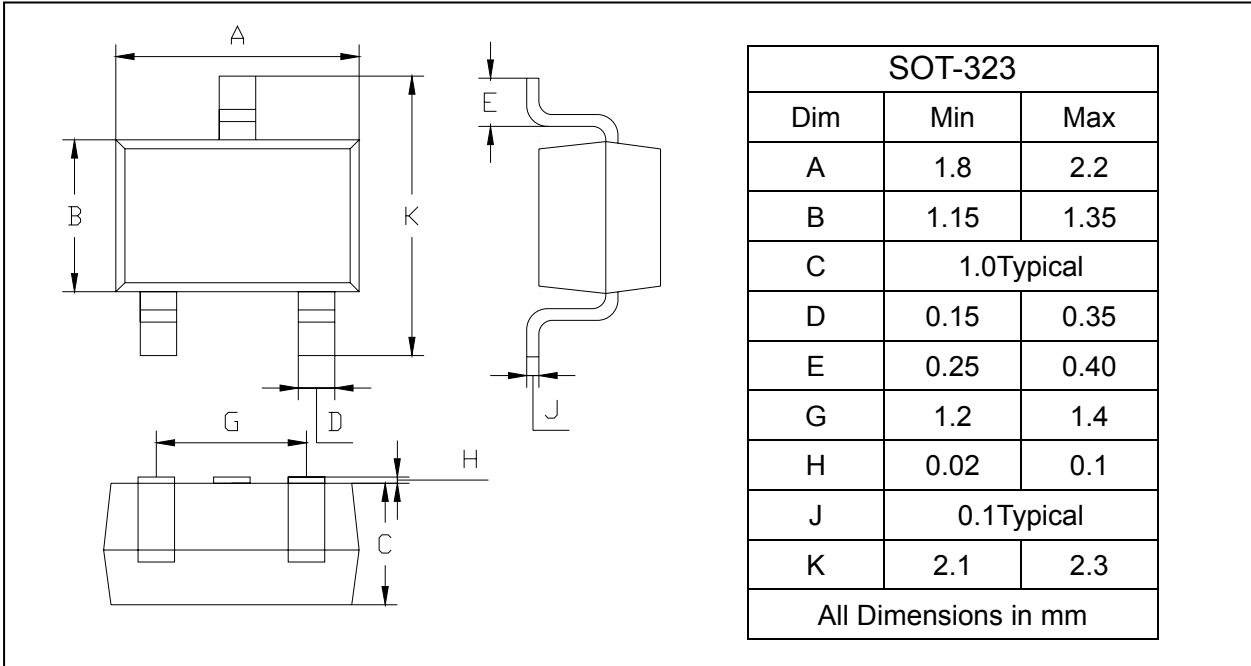
NPN Silicon Epitaxial Planar Transistor

2PD601AW

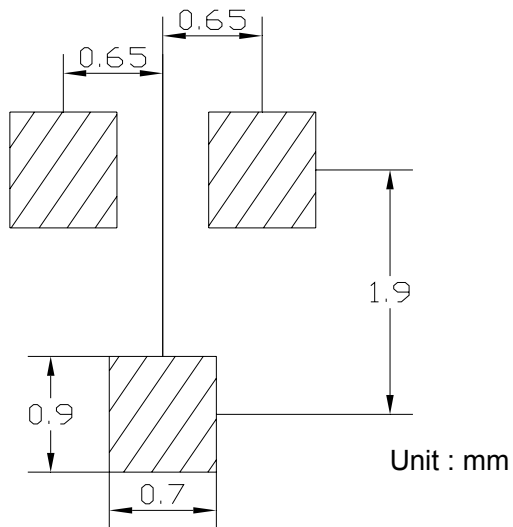
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2PD601AW	SOT-323	3000/Tape&Reel